

Docket: 740819-617
Reissue Application No. 09/986,997
Page 2

AMENDMENT TO THE CLAIMS

Please amend the claim as follows:

39. (Amended) A method for fabricating a semiconductor device, comprising the steps of:

a) forming a semiconductor layer of a Group III nitride containing a dopant over a substrate;

b) forming a p-side electrode out of a metal on the semiconductor layer;
and

c) after introducing the substrate into a vacuum chamber, charging plasma into the vacuum chamber to form an ambient of plasma while keeping the temperature of the substrate at about 600°C or lower, thereby making the conductivity type of the semiconductor layer p-type,

wherein the ambient of the plasma includes nitrogen plasma.